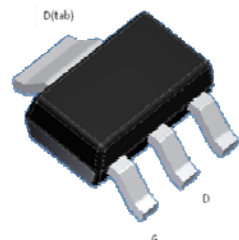


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	250V
$R_{DS(on)} (MAX.)$	$1\ \Omega$
I_D	1.1A



UIS, 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\ ^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\ ^\circ\text{C}$	I_D	1.1	A
	$T_C = 100\ ^\circ\text{C}$		0.7	
Pulsed Drain Current ¹		I_{DM}	4.4	
Power Dissipation	$T_C = 25\ ^\circ\text{C}$	P_D	6.25	W
	$T_C = 100\ ^\circ\text{C}$		2.5	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		20	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		150	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS ($T_c = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	250			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	2.0	3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$			1	μA
		$V_{DS} = 200V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	1.1			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.55A$		0.82	1.0	Ω
		$V_{GS} = 5V, I_D = 0.3A$		0.90	1.1	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 0.55A$		2.3		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		1224		pF
Output Capacitance	C_{oss}			27		
Reverse Transfer Capacitance	C_{rss}			23		
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 200V, V_{GS} = 10V, I_D = 0.55A$		32		nC
Gate-Source Charge ^{1,2}	Q_{gs}			4		
Gate-Drain Charge ^{1,2}	Q_{gd}			8.1		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 100V, I_D = 0.5A, V_{GS} = 10V, R_{GS} = 6\Omega$		10		nS
Rise Time ^{1,2}	t_r			50		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			20		
Fall Time ^{1,2}	t_f			45		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I_S				1.1	A
Pulsed Current ³	I_{SM}				4.4	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.5	V

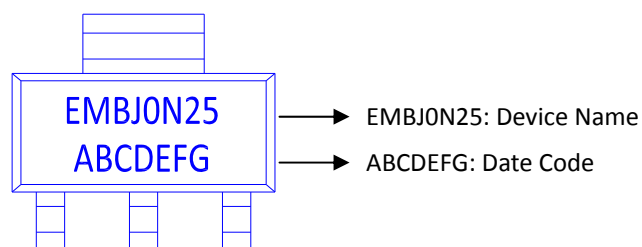
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

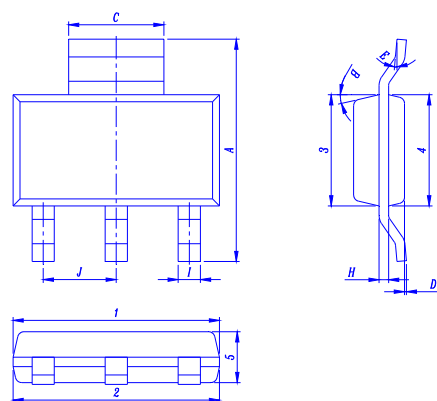
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMBJ0N25Q for SOT-223



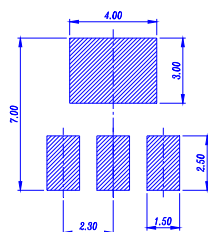
Outline Drawing



Dimension in mm

Dimension	A	C	D	E	I	H	B	J	1	2	3	4	5
Min.	6.70	2.90	0.02	0°	0.60	0.25			6.30	6.30	3.30	3.30	1.40
Typ.							13°	2.30					
Max.	7.30	3.10	0.10	10°	0.80	0.35			6.90	6.70	3.70	3.70	1.80

Recommended minimum pads





TYPICAL CHARACTERISTICS

